

Silicon Diode

FEPF16DT

Fast Efficient Rectifier

200V / 16A

DATASHEET

from

www.web-bcs.com

OEM – General Semiconductor

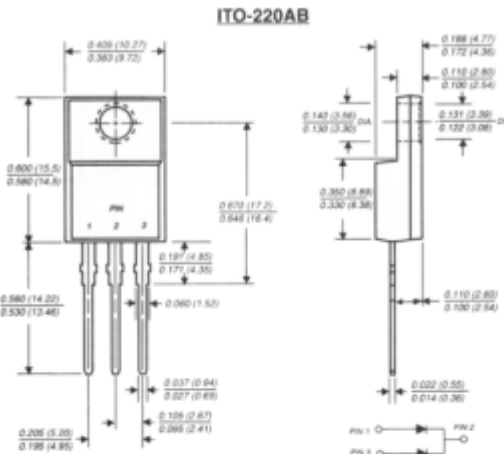
Source: General Semiconductor Databook 1998

NEW PRODUCT NEW PRODUCT NEW PRODUCT

FEPF16AT THRU FEPF16JT

FAST EFFICIENT PLASTIC RECTIFIER

Reverse Voltage - 50 to 600 Volts Forward Current - 16.0 Amperes



Dimensions are in inches and (millimeters)

FEATURES

- ◆ Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- ◆ Dual rectifier construction, positive centertap
- ◆ Glass passivated chip junctions
- ◆ Low power loss
- ◆ Low forward voltage, high current capability
- ◆ High surge current capability
- ◆ Superfast recovery times for high efficiency
- ◆ High temperature soldering guaranteed: 250°C, 0.25" (6.35mm) from case for 10 seconds



MECHANICAL DATA

Case: JEDEC TO-220AB molded plastic body
Terminals: Plated leads solderable per MIL-STD-750, Method 2026
Polarity: As marked
Mounting Position: Any
Weight: 0.08 ounce, 2.24 grams
Mounting Torque: 5 in. - lbs. max.

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

	SYMBOLS	FEPF 16AT	FEPF 16BT	FEPF 16CT	FEPF 16DT	FEPF 16FT	FEPF 16GT	FEPF 16HT	FEPF 16JT	UNITS
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	150	200	300	400	500	600	Volts
Maximum RMS voltage	V _{RMS}	35	70	105	140	210	280	350	420	Volts
Maximum DC blocking voltage	V _{DC}	50	100	150	200	300	400	500	600	Volts
Maximum average forward rectified current at T _C =100°C	I _(AV)	16.0								Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) at T _C =100°C	I _{FSM}	200.0								Amps
Maximum instantaneous forward voltage per leg at 8.0A	V _F	0.95			1.3		1.5			Volts
Maximum DC reverse current at rated DC blocking voltage per leg	I _R	10.0				500.0				µA
Maximum reverse recovery time (NOTE 1) per leg	t _{rr}	35.0			50.0					ns
Typical junction capacitance per leg (NOTE 2)	C _J	85.0				60.0				pF
Typical thermal resistance (NOTE 3)	R _{θJC}	5.0								°C/W
Operating junction and storage temperature range	T _J , T _{STG}	-55 to +150								°C

NOTES:
 (1) Reverse recovery test conditions: I_R=0.5A, I_R=1.0A, I_F=0.25A
 (2) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts
 (3) Thermal resistance from junction to case per leg mounted on heatsink

RATINGS AND CHARACTERISTICS CURVES FEFP16AT THRU FEFP16JT

